IN THE CLAIMS:

Please substitute the following claims for the same-numbered claims in the application:

1-3. (Canceled).

4. (Currently Amended) ~~The semiconductor structure in claim 1,~~ A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate; and

a first gate dielectric covering opposing sides of said first fin and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness, wherein said first thickness is different from said second thickness and wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

5. (Currently Amended) ~~The semiconductor structure in claim 1,~~ A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate;

~~further comprising~~ a cap over said fins; and

PAGE 2/7 * RCVD AT 6/27/2006 1:40:01 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-6/46 * DNIS:2738300 * CSID:3012618825 * DURATION (mm-ss):02-02

a first gate dielectric covering opposing sides of said first fin and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness and wherein said first thickness is different from said second thickness.

6. (Previously Presented) The semiconductor structure in claim 5, wherein said cap comprises a different material than said first gate dielectric and said second gate dielectric.

7-9. (Canceled).

10. (Currently Amended) ~~The semiconductor structure in claim 7,~~ A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate, wherein each of said fins comprises a central channel region and source and drain regions on opposite ends of said channel region; and

a first gate dielectric covering opposing sides of said channel region of said first fin and a second gate dielectric covering opposing sides of said channel region of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness,

wherein said first thickness is different from said second thickness,

wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric, and

wherein said fins have different thicknesses.

PAGE 3/7 * RCVD AT 6/27/2006 1:40:01 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-6/46 * DNIS:2738300 * CSID:3012618825 * DURATION (mm-ss):02-02

11. (Currently Amended) ~~The semiconductor structure in claim 7,~~ A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:

a substrate;

fins, comprising at least one first fin and at least one second fin, extending from said substrate, wherein each of said fins comprises a central channel region and source and drain regions on opposite ends of said channel region;

~~further comprising~~ a cap over said fins; and

a first gate dielectric covering opposing sides of said channel region of said first fin and a second gate dielectric covering opposing sides of said channel region of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness. wherein said first thickness is different from said second thickness and wherein said fins have different thicknesses.

12. (Previously Presented) The semiconductor structure in claim 11, wherein said cap comprises a different material than said first gate dielectric and said second gate dielectric.

13-14. (Canceled).

15. (Currently Amended) ~~The semiconductor structure in claim 13,~~ A semiconductor structure having multiple fin-type field effect transistors (FinFETs), said semiconductor structure comprising:

a substrate;

complementary transistors on said substrate, wherein said complementary transistors comprise:

a first fin for a first type transistor and a second fin for a second type transistor extending from said substrate; and

PAGE 4/7 * RCVD AT 6/27/2006 1:40:01 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-6/46 * DNIS:2738300 * CSID:3012618825 * DURATION (mm-ss):02-02

a first gate dielectric covering opposing sides of said first fin and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness,

wherein said first thickness is different from said second thickness and

wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

16. (Current Amended) ~~The semiconductor structure in claim 13,~~ A semiconductor structure having multiple fin-type field effect transistors (FinFETs), said semiconductor structure comprising:

a substrate;

complementary transistors on said substrate, wherein said complementary transistors comprise:

a first fin for a first type transistor and a second fin for a second type transistor extending from said substrate;

~~further comprising~~ a cap over said fins; and

a first gate dielectric covering opposing sides of said first fin and a second gate dielectric covering opposing sides of said second fin,

wherein said first gate dielectric has a first thickness and said second gate dielectric has a second thickness and wherein said first thickness is different from said second thickness.

17. (Currently Amended) The semiconductor structure in claim [[13]] 16, wherein said cap comprises a different material than said first gate dielectric and said second gate dielectric.

18-34. (Canceled).

PAGE 5/7 * RCVD AT 6/27/2006 1:40:01 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-6/46 * DNIS:2738300 * CSID:3012618825 * DURATION (mm-ss):02-02